FX20KMJ-3

High-Speed Switching Use
Pch Power MOS FET

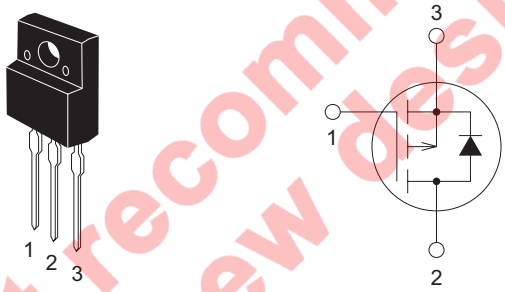
REJ03G1444-0200
(Previous: MEJ02G0289-0101)
Rev.2.00
Aug 07, 2006

Features

- Drive voltage : 4 V
- V_{DSS} : –150 V
- $r_{DS(ON)\ (max)}$: 0.29 Ω
- I_D : –20 A
- Integrated Fast Recovery Diode (TYP.) : 100 ns
- Viso : 2000 V

Outline

RENESAS Package code: PRSS0003AB-A
(Package name: TO-220FN)



1. Gate
2. Drain
3. Source

Applications

Motor control, Lamp control, Solenoid control, DC-DC converters, etc.

Maximum Ratings

(Tc = 25°C)

Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V_{DSS}	–150	V	V_{GS} = 0 V
Gate-source voltage	V_{GSS}	±20	V	V_{DS} = 0 V
Drain current	I_D	–20	A	
Drain current (Pulsed)	I_{DM}	–80	A	
Avalanche drain current (Pulsed)	I_{DA}	–20	A	L = 30 µH
Source current	I_S	–20	A	
Source current (Pulsed)	I_{SM}	–80	A	
Maximum power dissipation	P_D	30	W	
Channel temperature	Tch	– 55 to +150	°C	
Storage temperature	Tstg	– 55 to +150	°C	
Isolation voltage	Viso	2000	V	AC for 1 minute, Terminal to case
Mass	—	2.0	g	Typical value

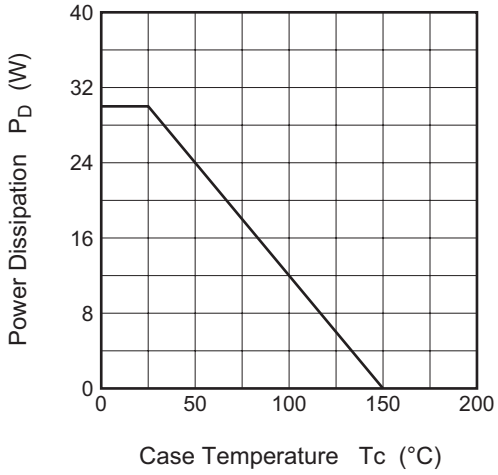
Electrical Characteristics

(Tch = 25°C)

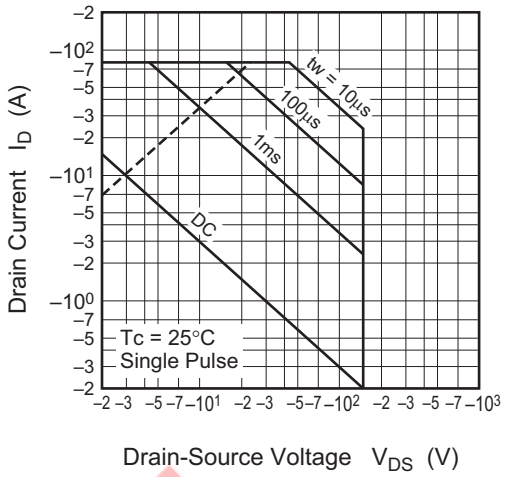
Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain-source breakdown voltage	$V_{(BR)DSS}$	–150	—	—	V	I_D = –1 mA, V_{GS} = 0 V
Gate-source leakage current	I_{GSS}	—	—	±0.1	µA	V_{GS} = ±20 V, V_{DS} = 0 V
Drain-source leakage current	I_{DSS}	—	—	–0.1	mA	V_{DS} = –150 V, V_{GS} = 0 V
Gate-source threshold voltage	$V_{GS(th)}$	–1.3	–1.8	–2.3	V	I_D = –1 mA, V_{DS} = –10 V
Drain-source on-state resistance	$r_{DS(ON)}$	—	0.23	0.29	Ω	I_D = –10 A, V_{GS} = –10 V
Drain-source on-state resistance	$r_{DS(ON)}$	—	0.25	0.32	Ω	I_D = –10 A, V_{GS} = – 4 V
Drain-source on-state voltage	$V_{DS(ON)}$	—	–2.3	–2.9	V	I_D = –10 A, V_{GS} = –10 V
Forward transfer admittance	$\lvert y_{fs} \rvert$	—	17.5	—	S	I_D = –10 A, V_{DS} = –10 V
Input capacitance	Ciss	—	4470	—	pF	V_{DS} = –10 V, V_{GS} = 0 V, f = 1MHz
Output capacitance	Coss	—	248	—	pF	
Reverse transfer capacitance	Crss	—	115	—	pF	
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	V_{DD} = –80 V, I_D = –10 A, V_{GS} = –10 V, R_{GEN} = R_{GS} = 50 Ω
Rise time	t_r	—	42	—	ns	
Turn-off delay time	$t_{d(off)}$	—	273	—	ns	
Fall time	t_f	—	114	—	ns	
Source-drain voltage	V_{SD}	—	–1.0	–1.5	V	I_S = –10 A, V_{GS} = 0 V
Thermal resistance	$R_{th(ch-c)}$	—	—	4.17	°C/W	Channel to case
Reverse recovery time	t_{rr}	—	100	—	ns	I_S = –20 A, d_{is}/d_t = 100 A/µs

Performance Curves

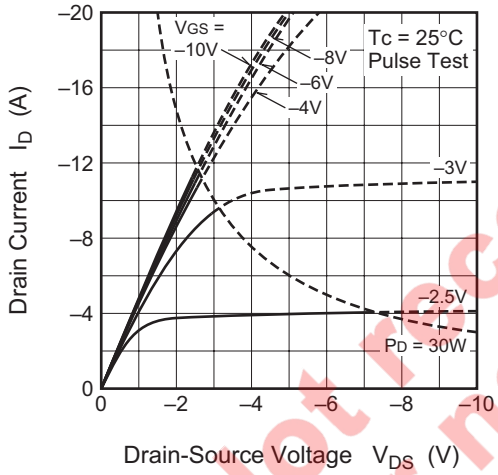
Power Dissipation Derating Curve



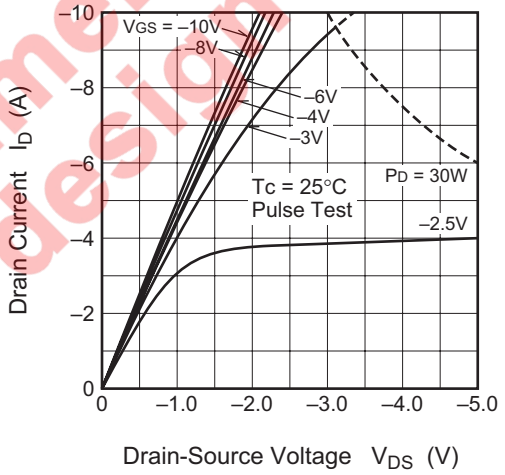
Maximum Safe Operating Area



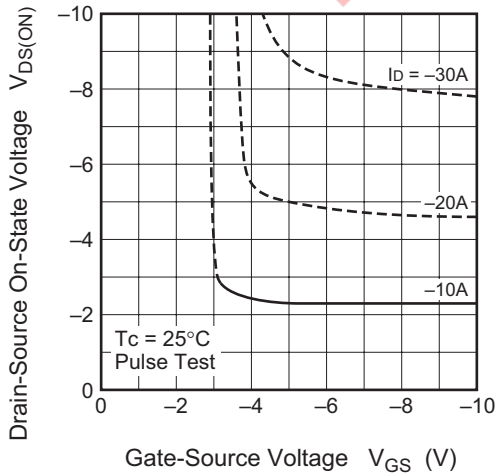
Output Characteristics (Typical)



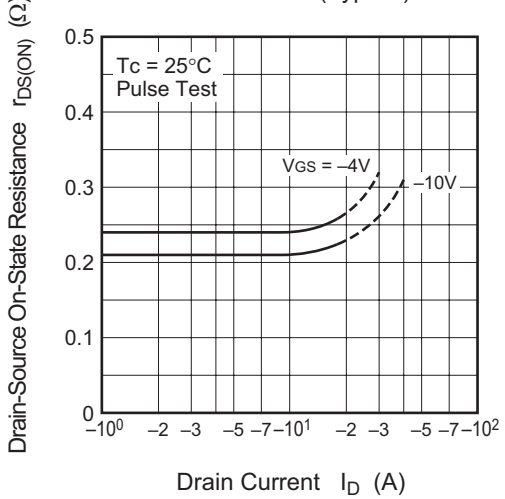
Output Characteristics (Typical)



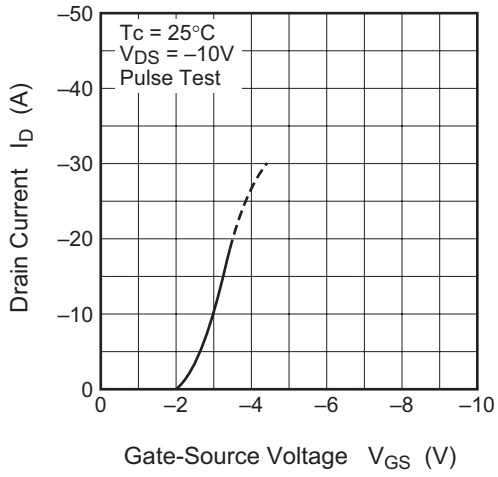
On-State Voltage vs.
Gate-Source Voltage (Typical)



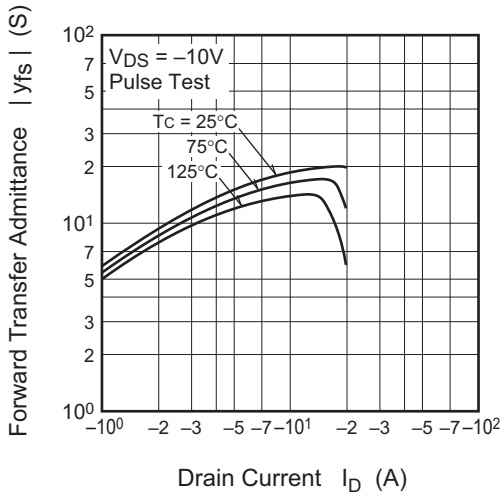
On-State Resistance vs.
Drain Current (Typical)



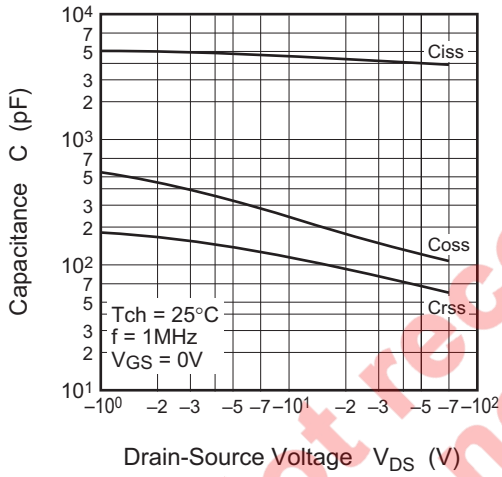
Transfer Characteristics (Typical)



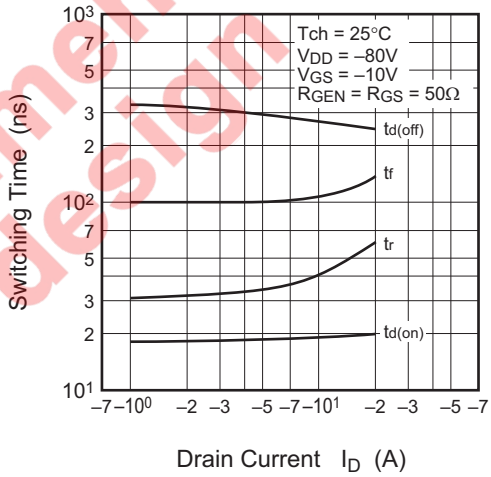
Forward Transfer Admittance vs. Drain Current (Typical)



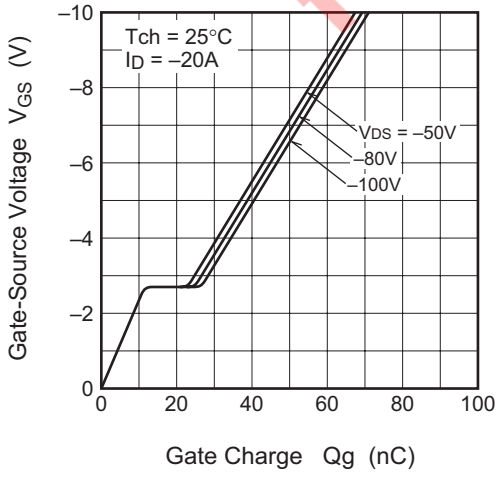
Capacitance vs. Drain-Source Voltage (Typical)



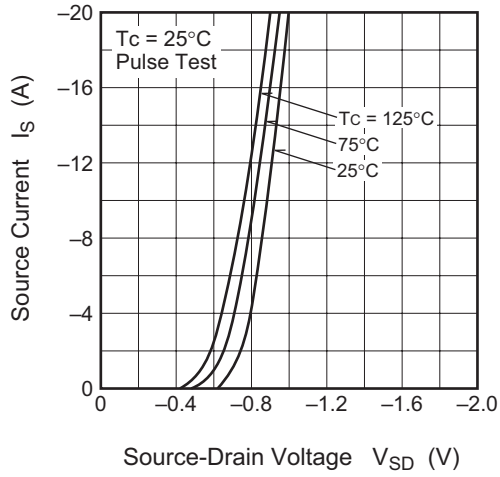
Switching Characteristics (Typical)



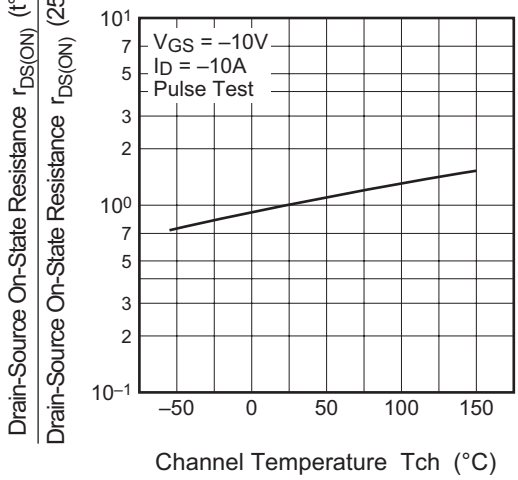
Gate-Source Voltage vs. Gate Charge (Typical)



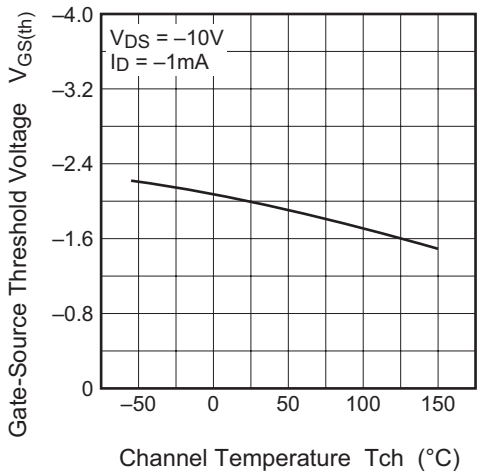
Source-Drain Diode Forward Characteristics (Typical)



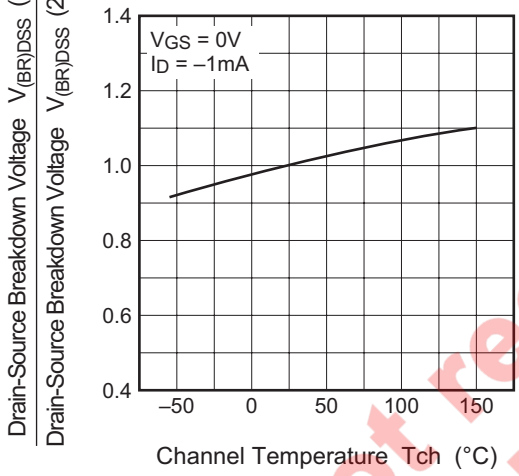
On-State Resistance vs. Channel Temperature (Typical)



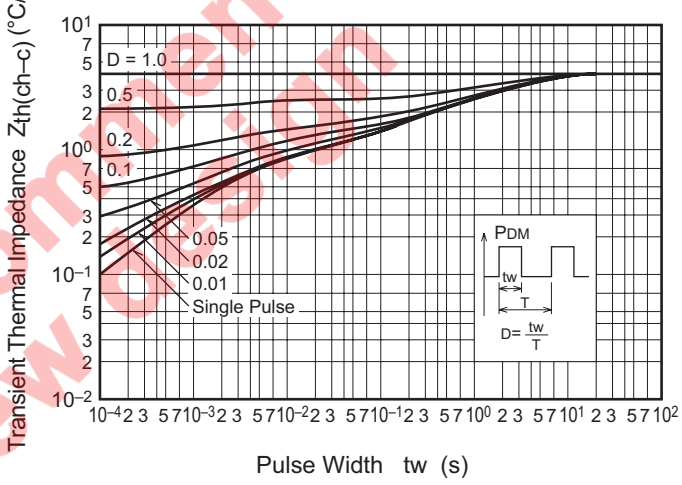
Threshold Voltage vs. Channel Temperature (Typical)



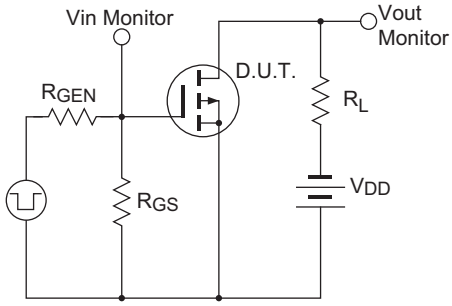
Breakdown Voltage vs. Channel Temperature (Typical)



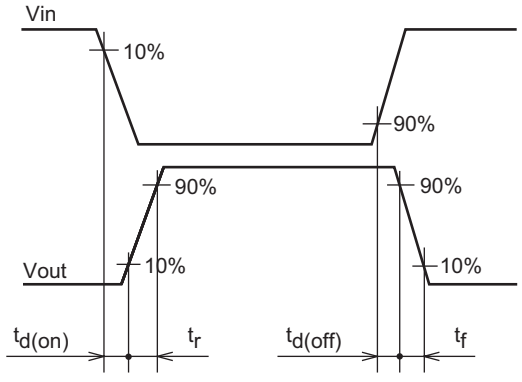
Transient Thermal Impedance Characteristics



Switching Time Measurement Circuit



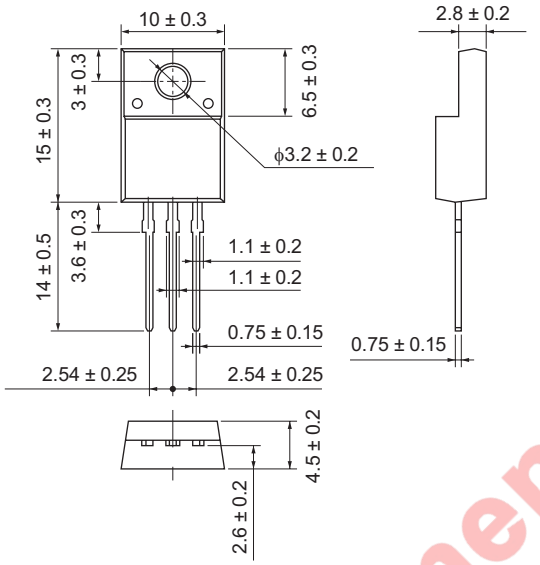
Switching Waveform



Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
TO-220FN	—	PRSS0003AB-A	—	2.0g

Unit: mm



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	50	Type name	FX20KMJ-3
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	FX20KMJ-3-A8

Note: Please confirm the specification about the shipping in detail.

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